High permittivity, low loss microwave dielectrics suitable for 5G resonator and low temperature co-fired ceramic architecture

Di Zhou*^{a,b}, Li-Xia Pang^{a,c}, Da-Wei Wang^a, Chun Li^d, Biao-Bing Jin^d & Ian M. Reaney*^a

^aDepartment of Materials Science and Engineering, University of Sheffield, S1 3JD,

UK

^bElectronic Materials Research Laboratory, Key Laboratory of the Ministry of

Education & International Center for Dielectric Research, Xi'an Jiaotong University,

Xi'an 710049, Shaanxi, China

^cMicro-optoelectronic Systems Laboratories, Xi'an Technological University, Xi'an 710032, Shaanxi, China

^dResearch Institute of Superconductor Electronics (RISE), School of Electronic Science and Engineering, Nanjing University, Nanjing, Jiangsu, 210093, China.

^{*}Corresponding author E-mail address: i.m.reaney@sheffield.ac.uk (Ian M. Reaney) & zhoudi1220@gmail.com (Di Zhou)

Supplemental Information



Figure S1. The experimental (circles) and simulated (line) XRD patterns of the Bi₂(Li_{0.5}Ta_{1.5})O₇ composition sintered at 1025 °C using space group C 1 2/c 1 (15) (R_p = 15.2 %, R_{wp} = 16.6 %, R_{exp} = 11.3 %) (b) (The short vertical lines represent Bragg reflection positions. The continuous line at the bottom shows the difference between experimental and simulated intensity)

Fig. S1 shows the experimental (circles) and simulated (line) XRD patterns of the $Bi_2(Li_{0.5}Ta_{1.5})O_7$ composition sintered at 1025 °C using space group C 1 2/c 1 (15) (R_p = 15.2 %, R_{wp} = 16.6 %, R_{exp} = 11.3 %). Cell parameters were calculated as a=13.043 Å, b=7.595 Å, c=12.268 Å and beta angle=101.425 degree.